

# BC817-40W

## 45 V, 0.5 A, General Purpose NPN Transistor

ON Semiconductor's BC817-40W is a General Purpose NPN Transistor that is housed in the SC-70/SOT-323 package.

### Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	45	V
Collector – Base Voltage	$V_{CBO}$	50	V
Emitter – Base Voltage	$V_{EBO}$	5.0	V
Collector Current – Continuous	$I_C$	500	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1)	$P_D$	460	mW
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	272	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

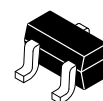
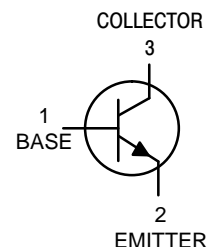
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 Board, 1 oz. Cu, 100 mm<sup>2</sup>



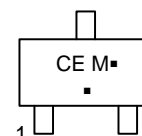
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)



SC-70  
CASE 419  
STYLE 3

### MARKING DIAGRAM



CE = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION†

Device	Package	Shipping
BC817-40WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
NSVBC817-40WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# BC817-40W

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ )	$V_{(VR)CEO}$	45	-	-	V
Collector-Emitter Breakdown Voltage ( $V_{EB} = 0\text{ V}$ , $I_C = 10\text{ }\mu\text{A}$ )	$V_{(VR)CES}$	50	-	-	V
Emitter-Base Breakdown Voltage ( $I_E = 1.0\text{ }\mu\text{A}$ )	$V_{(VR)EBO}$	5.0	-	-	V
Collector Cutoff Current ( $V_{CB} = 20\text{ V}$ ) ( $V_{CB} = 20\text{ V}$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	-	-	100 5.0	nA $\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
DC Current Gain (Note 2) ( $I_C = 100\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ ) ( $I_C = 500\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ )	$h_{FE}$	250 40	- -	600 -	-
Collector-Emitter Saturation Voltage (Note 2) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{CE(sat)}$	-	-	0.7	V
Base-Emitter On Voltage (Note 2) ( $I_C = 500\text{ mA}$ , $V_{CE} = 1.0\text{ V}$ )	$V_{BE(on)}$	-	-	1.2	V
<b>SMALL-SIGNAL CHARACTERISTICS</b>					
Current-Gain - Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ , $f = 100\text{ MHz}$ )	$f_T$	100	-	-	MHz
Output Capacitance ( $V_{CB} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	-	10	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Condition: Pulse Width = 300  $\mu\text{sec}$ , Duty Cycle  $\leq 2\%$

TYPICAL CHARACTERISTICS

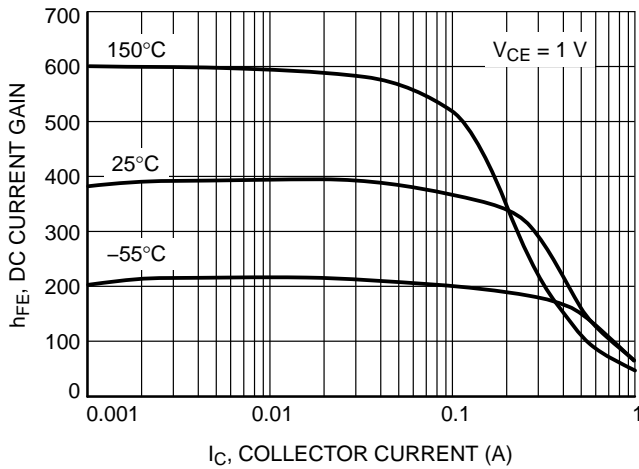


Figure 1. DC Current Gain vs. Collector Current

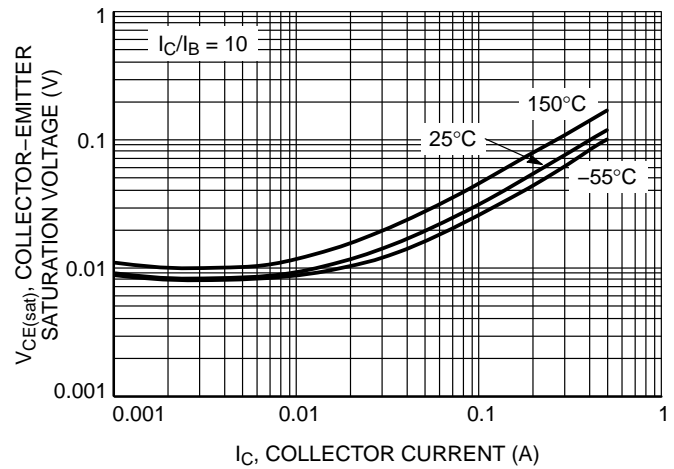


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

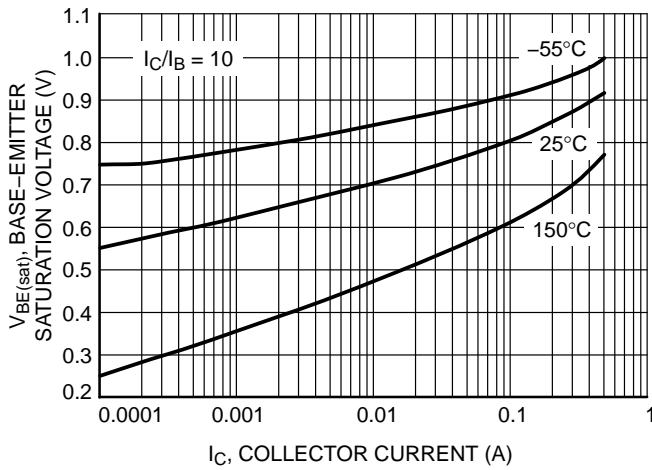


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

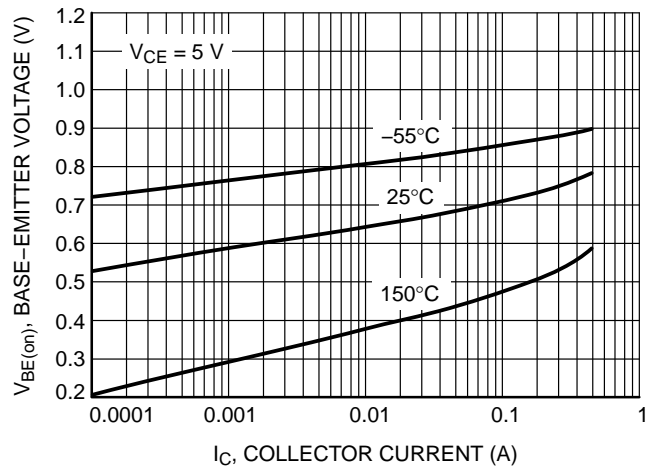


Figure 4. Base Emitter Voltage vs. Collector Current

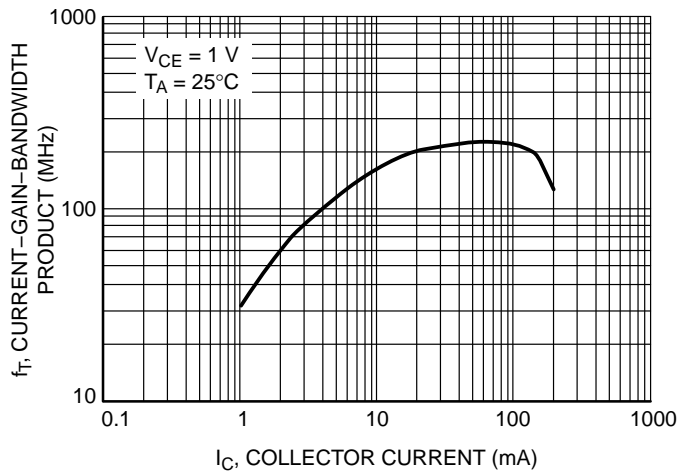


Figure 5. Current Gain Bandwidth Product vs. Collector Current

# BC817-40W

## TYPICAL CHARACTERISTICS

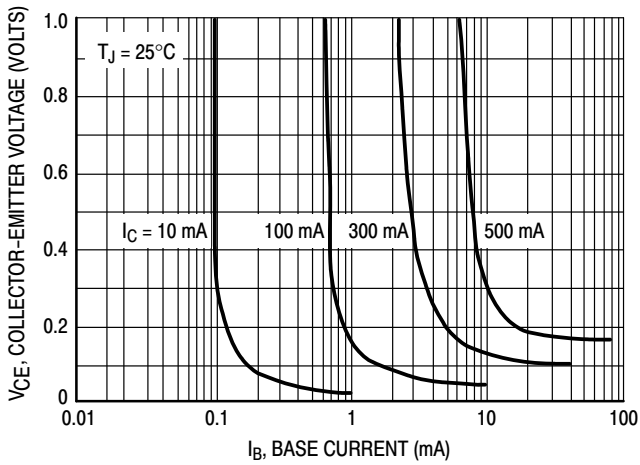


Figure 6. Saturation Region

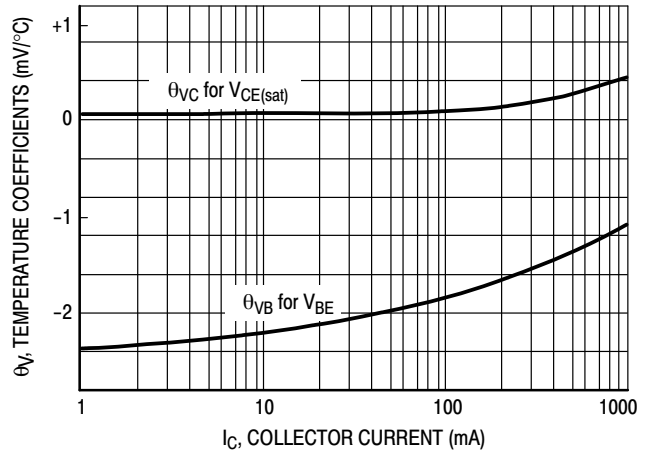


Figure 7. Temperature Coefficients

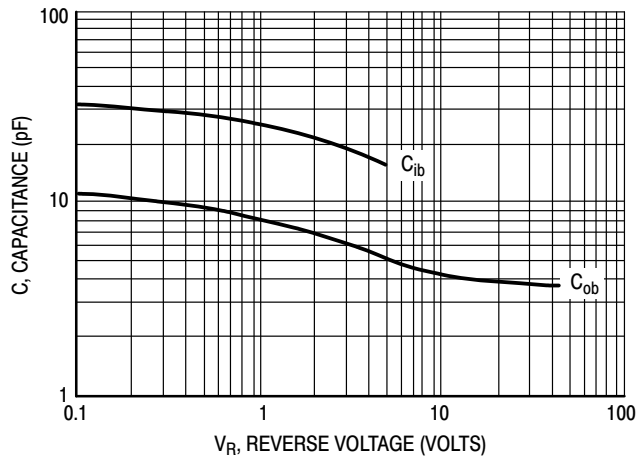


Figure 8. Capacitances

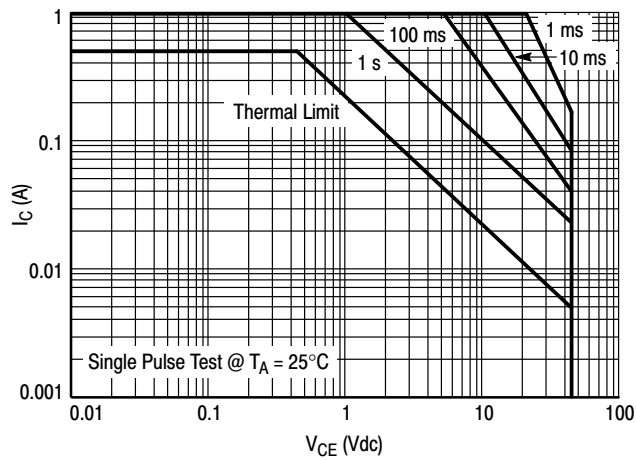
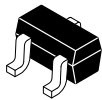


Figure 9. Safe Operating Area

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

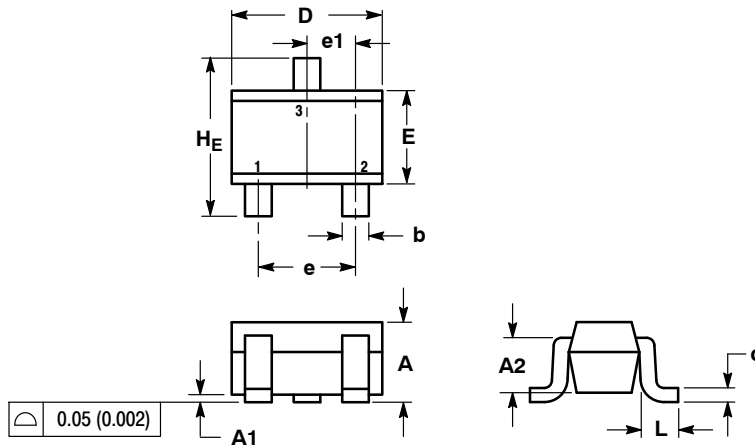
ON Semiconductor®



SCALE 4:1

SC-70 (SOT-323)  
CASE 419-04  
ISSUE N

DATE 11 NOV 2008

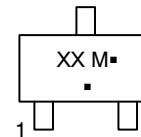


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

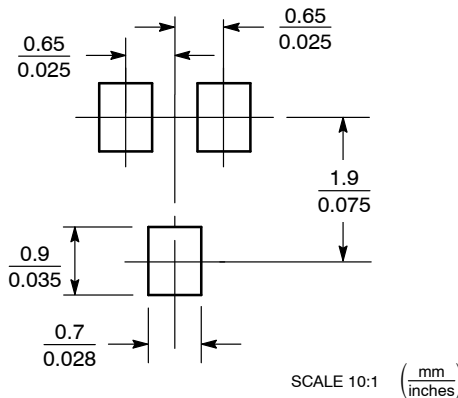
### GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:  
CANCELLED

STYLE 2:  
PIN 1. ANODE  
2. N.C.  
3. CATHODE

STYLE 3:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 6:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 7:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 8:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 9:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 10:  
PIN 1. CATHODE  
2. ANODE  
3. ANODE-CATHODE

STYLE 11:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

<b>DOCUMENT NUMBER:</b>	<b>98ASB42819B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SC-70 (SOT-323)</b>	<b>PAGE 1 OF 1</b>

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Email Requests to: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

### TECHNICAL SUPPORT

North American Technical Support:  
Voice Mail: 1 800-282-9855 Toll Free USA/Canada  
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative